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What is "Embedded - Microcontrollers"?

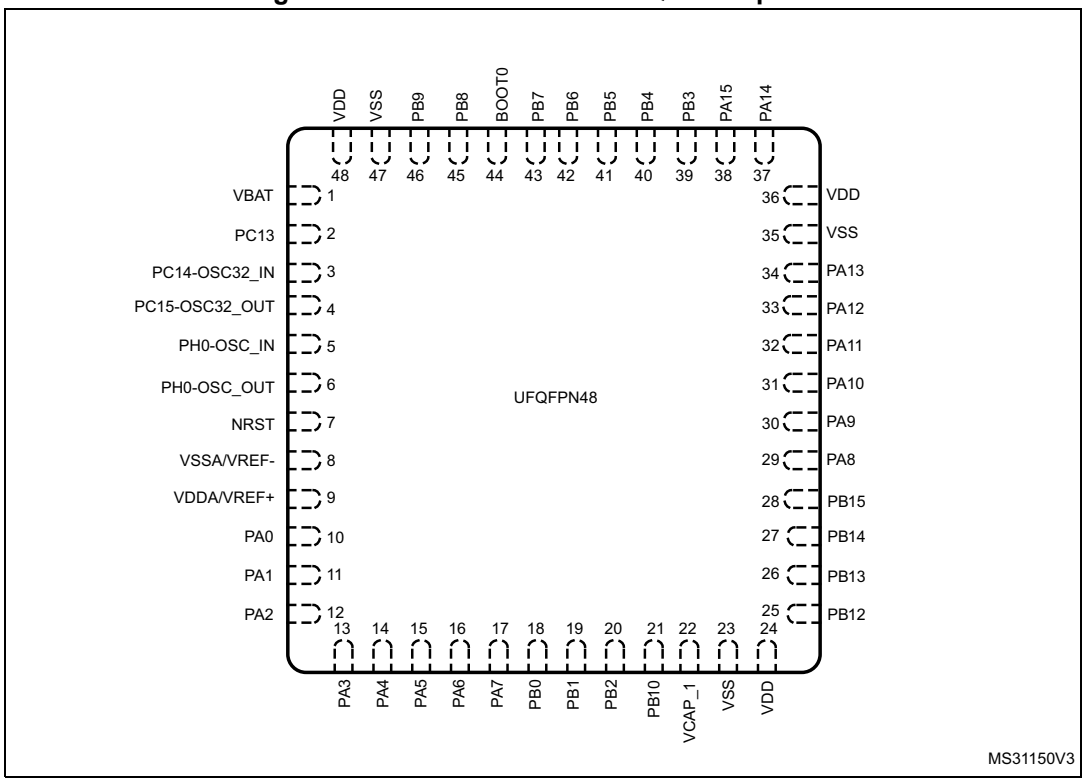
"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	100MHz
Connectivity	I²C, IrDA, LINbus, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	36
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	128K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f411ceu6tr

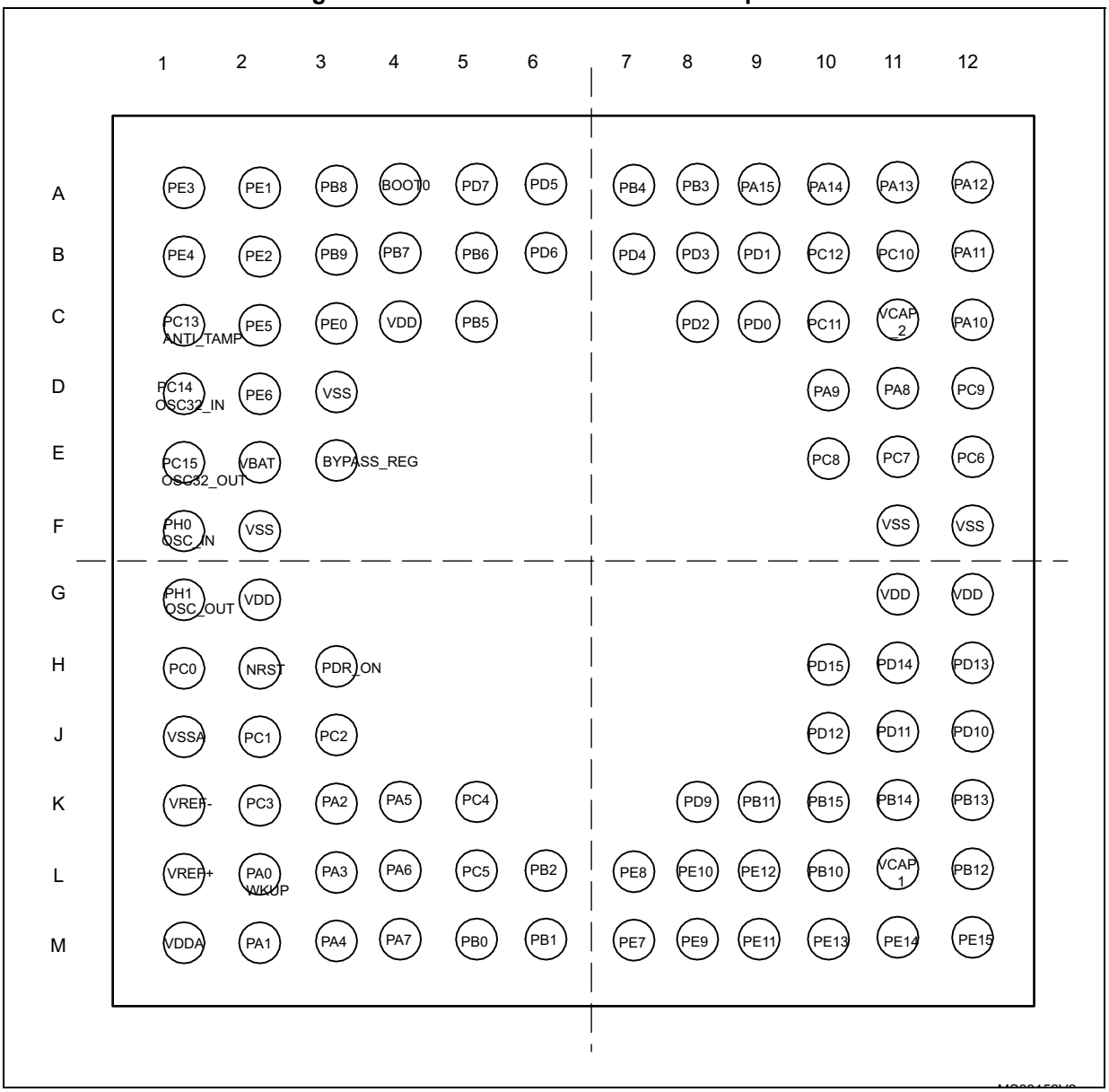
Contents

Figure 10. STM32F411xC/xE UFQFPN48 pinout



1. The above figure shows the package top view.

Figure 13. STM32F411xC/xE UFBGA100 pinout



1. This figure shows the package top view

Table 8. STM32F411xC/xE pin definitions (continued)

Pin number					Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UFQFPN48	LQFP64	WLCSP49	LQFP100	UFBGA100						
10	14	F6	23	L2	PA0-WKUP	I/O	TC	(5)	TIM2_CH1/TIM2_ET, TIM5_CH1, USART2_CTS, EVENTOUT	ADC1_0, WKUP1
11	15	G7	24	M2	PA1	I/O	FT	-	TIM2_CH2, TIM5_CH2, SPI4_MOSI/I2S4_SD, USART2_RTS, EVENTOUT	ADC1_1
12	16	E5	25	K3	PA2	I/O	FT	-	TIM2_CH3, TIM5_CH3, TIM9_CH1, I2S2_CKIN, USART2_TX, EVENTOUT	ADC1_2
13	17	E4	26	L3	PA3	I/O	FT	-	TIM2_CH4, TIM5_CH4, TIM9_CH2, I2S2_MCK, USART2_RX, EVENTOUT	ADC1_3
-	18	-	27	-	VSS	S	-	-	-	-
-	-	-	-	E3	BYPASS_REG	S	-	-	-	-
-	19	-	28	-	VDD	I	FT	-	EVENTOUT	-
14	20	G6	29	M3	PA4	I/O	FT	-	SPI1_NSS/I2S1_WS, SPI3_NSS/I2S3_WS, USART2_CK, EVENTOUT	ADC1_4
15	21	F5	30	K4	PA5	I/O	FT	-	TIM2_CH1/TIM2_ET, SPI1_SCK/I2S1_CK, EVENTOUT	ADC1_5
16	22	F4	31	L4	PA6	I/O	FT	-	TIM1_BKIN, TIM3_CH1, SPI1_MISO, I2S2_MCK, SDIO_CMD, EVENTOUT	ADC1_6
17	23	F3	32	M4	PA7	I/O	FT	-	TIM1_CH1N, TIM3_CH2, SPI1_MOSI/I2S1_SD, EVENTOUT	ADC1_7

Table 9. Alternate function mapping (continued)

Port		AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
		SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/I2S1SPI2/ I2S2/SPI3/ I2S3	SPI2/I2S2/ SPI3/ I2S3/SPI4/ I2S4/SPI5/ I2S5	SPI3/I2S3/ USART1/ USART2	USART6	I2C2/ I2C3	OTG1_FS		SDIO			
Port E	PE0	-	-	TIM4_ETR	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE1	-	-		-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE2	TRACECLK	-	-	-	-	SPI4_SCK/I2S4_CK	SPI5_SCK/I2S5_CK	-	-	-	-	-	-	-	-	EVENT OUT
	PE3	TRACED0	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE4	TRACED1	-	-	-	-	SPI4_NSS/I2S4_WS	SPI5_NSS/I2S5_WS	-	-	-	-	-	-	-	-	EVENT OUT
	PE5	TRACED2	-	-	TIM9_CH1	-	SPI4_MISO	SPI5_MISO	-	-	-	-	-	-	-	-	EVENT OUT
	PE6	TRACED3	-	-	TIM9_CH2	-	SPI4_MOSI/I2S4_SD	SPI5_MOSI/I2S5_SD	-	-	-	-	-	-	-	-	EVENT OUT
	PE7	-	TIM1_ETR	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE8	-	TIM1_CH1N	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE9	-	TIM1_CH1	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE10	-	TIM1_CH2N	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PE11	-	TIM1_CH2	-	-	-	SPI4_NSS/I2S4_WS	SPI5_NSS/I2S5_WS	-	-	-	-	-	-	-	-	EVENT OUT
	PE12	-	TIM1_CH3N	-	-	-	SPI4_SCK/I2S4_CK	SPI5_SCK/I2S5_CK	-	-	-	-	-	-	-	-	EVENT OUT
	PE13	-	TIM1_CH3	-	-	-	SPI4_MISO	SPI5_MISO	-	-	-	-	-	-	-	-	EVENT OUT
	PE14	-	TIM1_CH4	-	-	-	SPI4_MOSI/I2S4_SD	SPI5_MOSI/I2S5_SD	-	-	-	-	-	-	-	-	EVENT OUT
	PE15	-	TIM1_BKIN	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT

5 Memory mapping

The memory map is shown in *Figure 14*.

Figure 14. Memory map

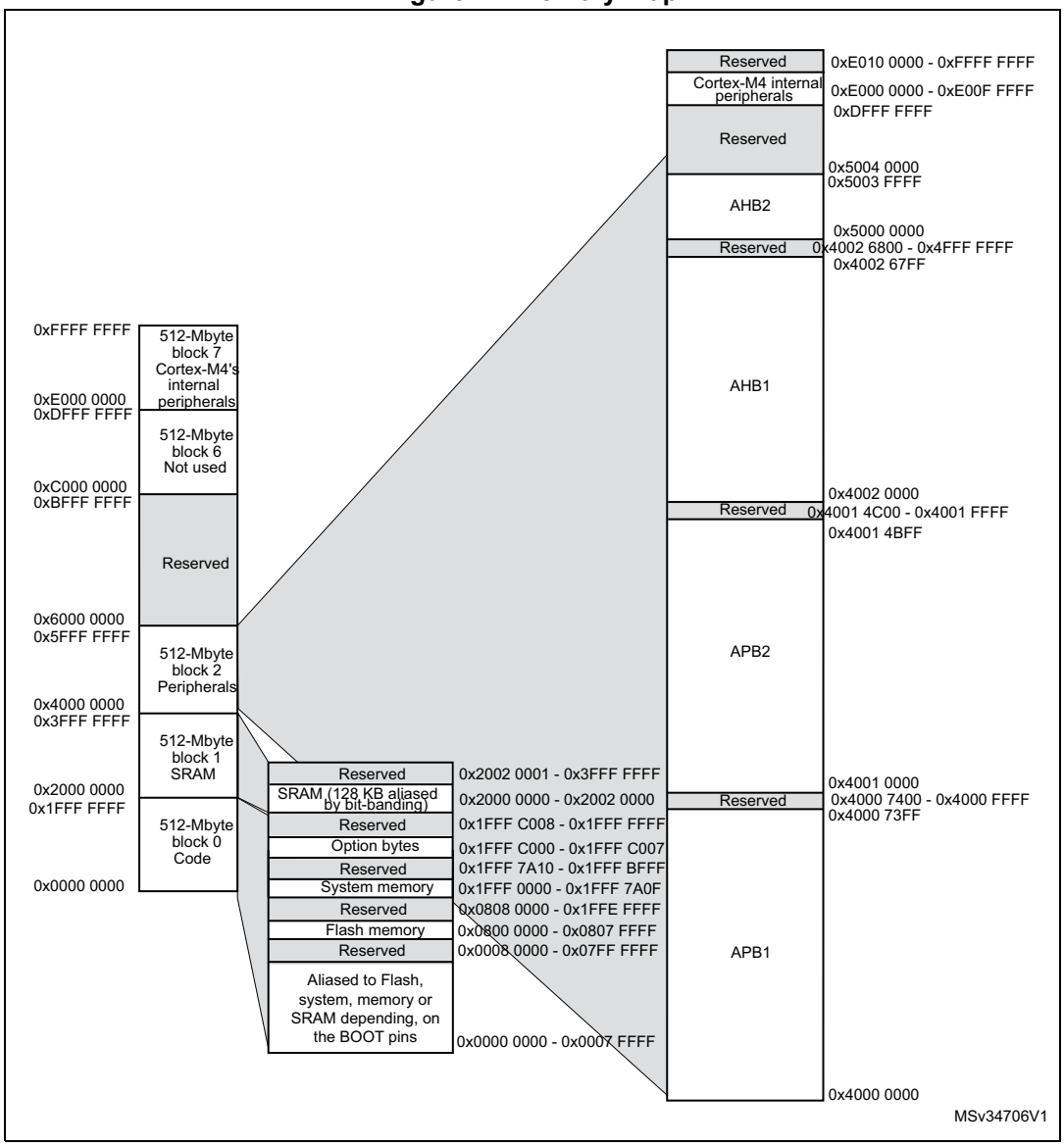


Table 10. STM32F411xC/xE register boundary addresses

Bus	Boundary address	Peripheral
	0xE010 0000 - 0xFFFF FFFF	Reserved
Cortex®-M4	0xE000 0000 - 0xE00F FFFF	Cortex-M4 internal peripherals
	0x5004 0000 - 0xDFFF FFFF	Reserved

Table 10. STM32F411xC/xE register boundary addresses (continued)

Bus	Boundary address	Peripheral
AHB2	0x5000 0000 - 0x5003 FFFF	USB OTG FS
AHB1	0x4002 6800 - 0x4FFF FFFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 4FFF	Reserved
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2000 - 0x4002 2FFF	Reserved
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1400 - 0x4002 1BFF	Reserved
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA

Table 21. Typical and maximum current consumption, code with data processing (ART accelerator disabled) running from SRAM - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)				Unit
					T_A= 25 °C	T_A= 85 °C	T_A= 105 °C	T_A= 125 °C	
I_{DD}	Supply current in **Run mode**	External clock, PLL ON(2), all peripherals enabled(3)(4)	100	21.7	23.3	23.9	24.3	25.3	mA
			84	17.5	19.2(5)	19.4	19.5	20.5	
			64	12.2	13.2	13.5	14.0	14.9	
			50	9.6	10.4	10.7	11.2	12.1	
			20	4.5	5.0	5.3	5.9	6.8	
		HSI, PLL OFF, all peripherals enabled(3)	16	3.0	3.3	3.6	4.3	5.2	
			1	0.5	0.7	1.0	1.7	2.6	
		External clock, PLL OFF(2), all peripherals disabled(3)	100	13.0	14.6(5)	14.6	14.9	16.0	
			84	10.5	11.9(5)	12.1	12.2	13.2	
			64	7.4	8.4(5)	8.8	8.9	9.9	
			50	5.9	6.6	6.8	7.3	8.2	
			20	2.8	3.3	3.5	4.2	5.1	
		HSI, PLL OFF, all peripherals disabled(3)	16	1.9	2.1	2.4	3.1	4.0	
			1	0.4	0.5	0.9	1.6	2.5	

1. Guaranteed by characterization results.
2. Refer to *Table 41* and RM0383 for the possible PLL VCO setting
3. When analog peripheral blocks such as ADC, HSE, LSE, HSI, or LSI are ON, an additional power consumption has to be considered.
4. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.
5. Guaranteed by test in production.

Table 26. Typical and maximum current consumption in Sleep mode - V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK} (MHz)	Typ	Max(1)				Unit
					T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD}	Supply current in **Sleep mode**	External clock, PLL ON(2), all peripherals enabled(3)(4)	100	12.2	13.2	13.4	14.1	15.3	mA
			84	9.8	10.6	10.9	11.6	12.8	
			64	6.9	7.4	7.7	8.3	9.5	
			50	5.4	5.9	6.2	6.8	8.0	
			20	2.8	3.2	3.5	4.1	5.3	
		HSI, PLL OFF(2), all peripherals enabled(3)	16	1.3	1.7	2.2	2.8	4.0	
			1	0.4	0.5	0.9	1.6	2.8	
		External clock, PLL ON(2) all peripherals disabled(3)	100	3.0	3.6	3.9	4.5	5.7	
			84	2.5	3.0	3.2	3.9	5.1	
			64	1.9	2.2	2.5	3.0	4.2	
			50	1.6	1.9	2.1	2.7	3.9	
			20	1.1	1.4	1.7	2.3	3.5	
		HSI, PLL OFF(2), all peripherals disabled(3)	16	0.4	0.5	0.9	1.6	2.8	
			1	0.3	0.4	0.8	1.5	2.7	

1. Guaranteed by characterization results.
2. Refer to *Table 41* and RM0383 for the possible PLL VCO setting.
3. Add an additional power consumption of 1.6 mA per ADC for the analog part. In applications, this consumption occurs only while the ADC is ON (ADON bit is set in the ADC_CR2 register).
4. When the ADC is ON (ADON bit set in the ADC_CR2), add an additional power consumption of 1.6mA per ADC for the analog part.

Table 27. Typical and maximum current consumptions in Stop mode - V_{DD} = 1.7 V

Symbol	Conditions	Parameter	Typ(1)	Max(1)				Unit
			T_A = 25 °C	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	T_A = 125 °C	
I_{DD_STOP}	Flash in Stop mode, all oscillators OFF, no independent watchdog	Main regulator usage	112	142(2)	400	710(2)	1200	µA
		Low power regulator usage	42.6	67(2)	300	580(2)	1044	
	Flash in Deep power down mode, all oscillators OFF, no independent watchdog	Main regulator usage	75	99(2)	310	580(2)	993	
		Low power regulator usage	13.6	37(2)	265	550(2)	1007	
		Low power low voltage regulator usage	9	28(2)	230	500(2)	910	

1. Guaranteed by characterization results.
2. Guaranteed by test in production.

Table 46. Flash memory programming with V_{PP} voltage (continued)

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{prog}	Programming voltage		2.7	-	3.6	V
V_{PP}	V_{PP} voltage range		7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin		10	-	-	mA
t_{VPP}(3)	Cumulative time during which V_{PP} is applied		-	-	1	hour

1. Guaranteed by design.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 47. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = - 40 to + 85 °C (temp. range 6) T_A = - 40 to + 105 °C (temp. range 7) T_A = - 40 to + 125 °C (temp. range 3)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		1 kcycle(2) at T_A = 125 °C	3	
		10 kcycle(2) at T_A = 55 °C	20	

1. Guaranteed by characterization results.
2. Cycling performed over the whole temperature range.

6.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 49*. They are based on the EMS levels and classes defined in application note AN1709.

Figure 35. SPI timing diagram - slave mode and CPHA = 1(1)

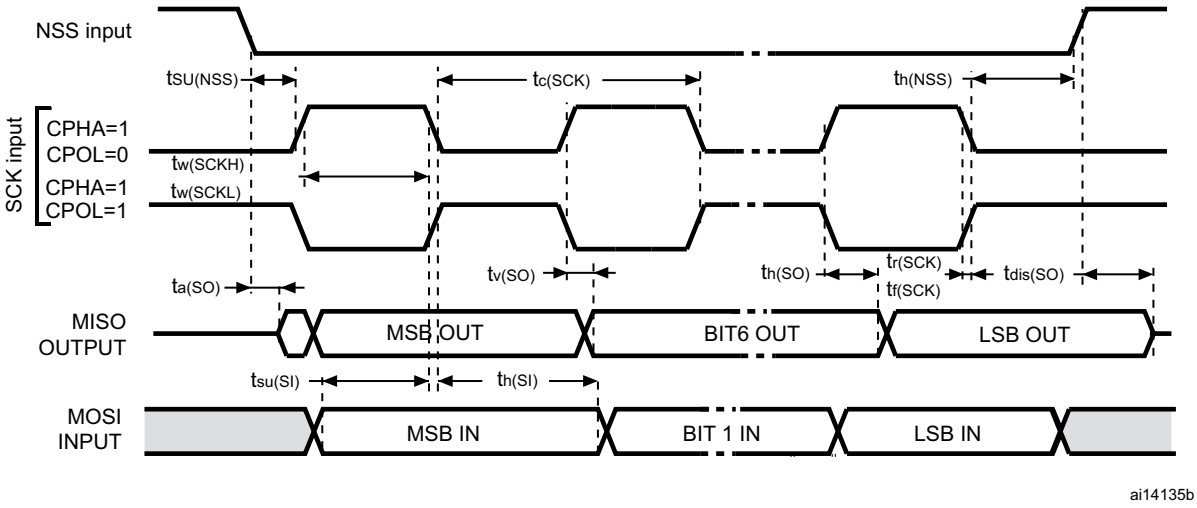
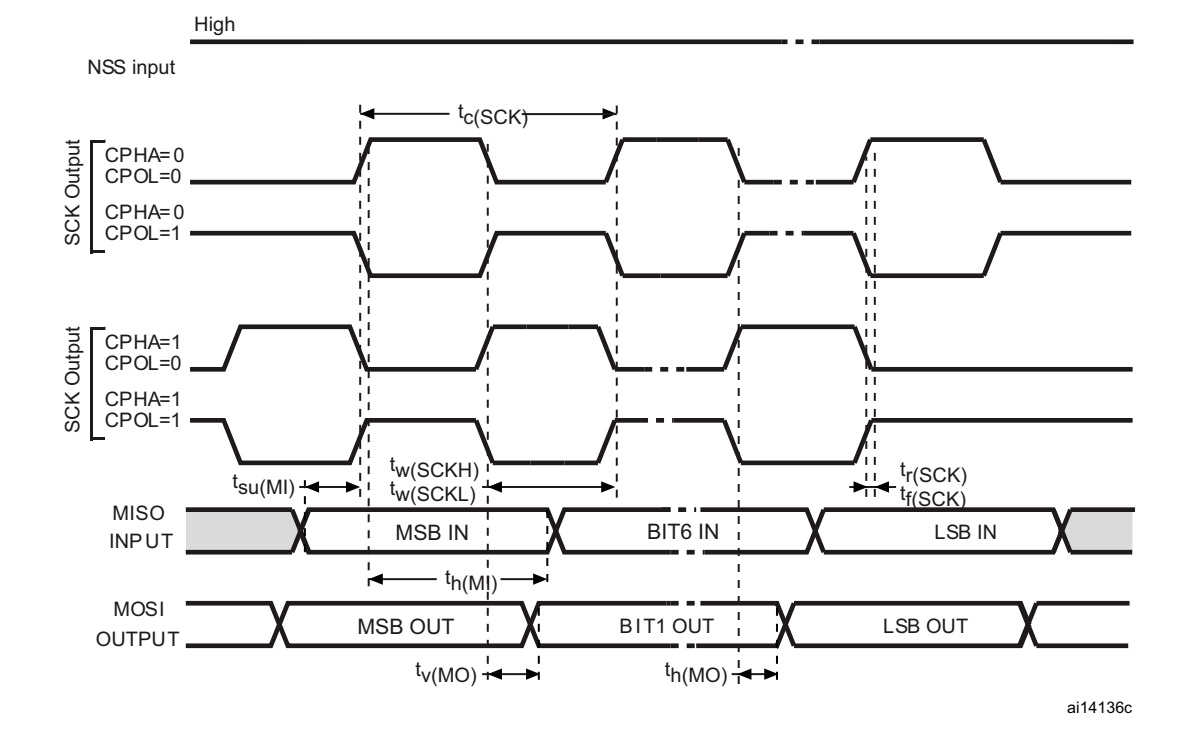


Figure 36. SPI timing diagram - master mode(1)



USB OTG full speed (FS) characteristics

This interface is present in USB OTG FS controller.

Table 62. USB OTG FS startup time

Symbol	Parameter	Max	Unit
$t_{STARTUP}$(1)	USB OTG FS transceiver startup time	1	µs

1. Guaranteed by design.

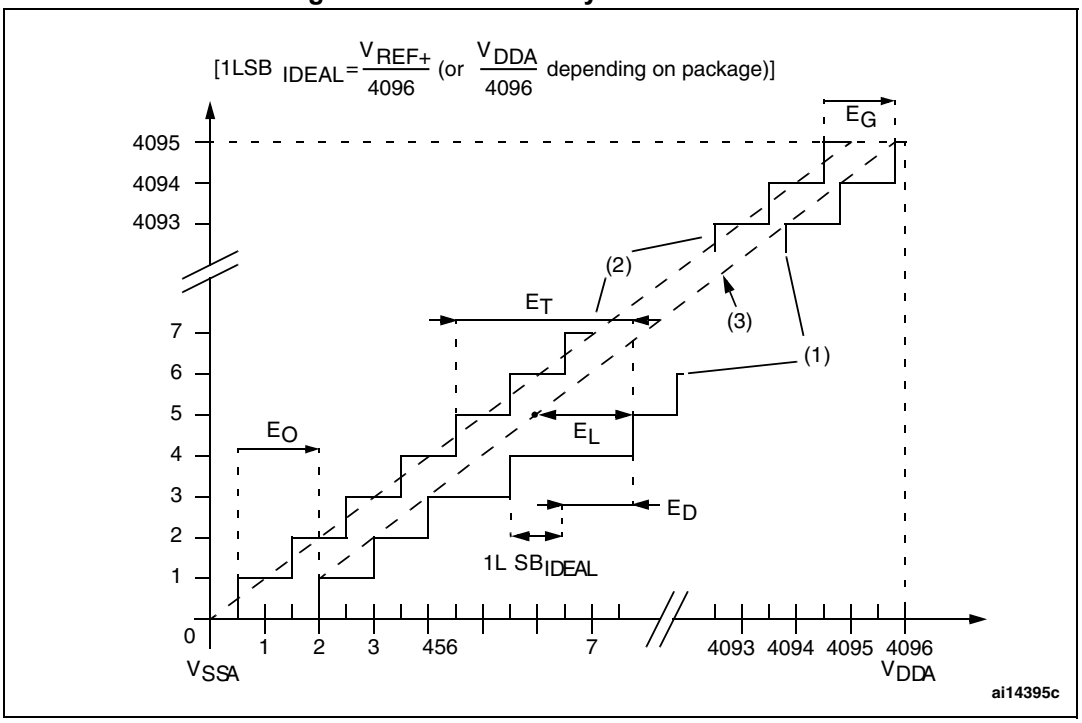
Table 63. USB OTG FS DC electrical characteristics

Symbol		Parameter	Conditions	Min.(1)	Typ.	Max.(1)	Unit
Input levels	V_{DD}	USB OTG FS operating voltage		3.0(2)	-	3.6	V
	V_{DI}(3)	Differential input sensitivity	I(USB_FS_DP/DM)	0.2	-	-	V
	V_{CM}(3)	Differential common mode range	Includes V_{DI} range	0.8	-	2.5	
	V_{SE}(3)	Single ended receiver threshold		1.3	-	2.0	
Output levels	V_{OL}	Static output level low	R_L of 1.5 kΩ to 3.6 V(4)	-	-	0.3	V
	V_{OH}	Static output level high	R_L of 15 kΩ to V_{SS}(4)	2.8	-	3.6	
R_{PD}		PA11, PA12 (USB_FS_DM/DP)	V_{IN} = V_{DD}	17	21	24	kΩ
		PA9 (OTG_FS_VBUS)		0.65	1.1	2.0	
R_{PU}		PA11, PA12 (USB_FS_DM/DP)	V_{IN} = V_{SS}	1.5	1.8	2.1	
		PA9 (OTG_FS_VBUS)	V_{IN} = V_{SS}	0.25	0.37	0.55	

1. All the voltages are measured from the local ground potential.
2. The USB OTG FS functionality is ensured down to 2.7 V but not the full USB full speed electrical characteristics which are degraded in the 2.7-to-3.0 V V_{DD} voltage range.
3. Guaranteed by design.
4. R_L is the load connected on the USB OTG FS drivers.

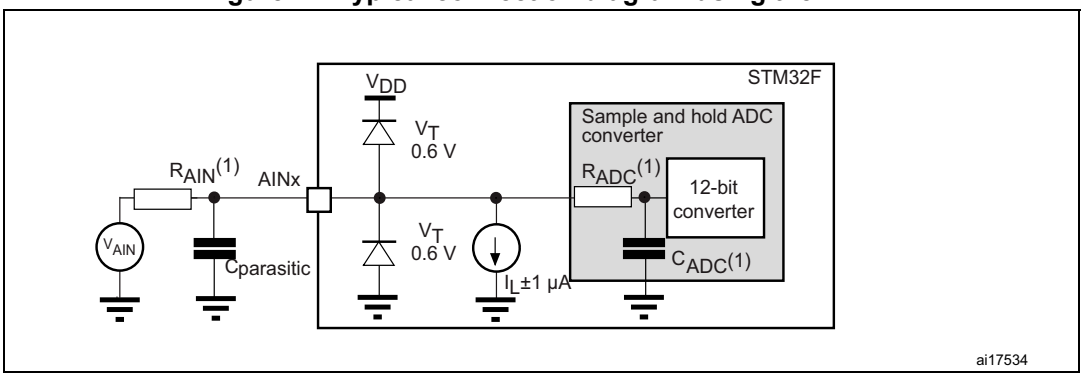
Note: When VBUS sensing feature is enabled, PA9 should be left at their default state (floating input), not as alternate function. A typical 200 µA current consumption of the embedded sensing block (current to voltage conversion to determine the different sessions) can be observed on PA9 when the feature is enabled.

Figure 40. ADC accuracy characteristics



1. See also *Table 67*.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 41. Typical connection diagram using the ADC



1. Refer to *Table 65* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

6.3.25 RTC characteristics

Table 77. Dynamic characteristics: eMMC characteristics V_{DD} = 1.7 V to 1.9 V(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PP}	Clock frequency in data transfer mode	-	0	-	50	MHz
-	SDIO_CK/fPCLK2 frequency ratio	-	-	-	8/3	-
$t_{W(CKL)}$	Clock low time	fpp = 50 MHz	10	10.5	-	ns
$t_{W(CKH)}$	Clock high time	fpp = 50 MHz	9	9.5	-	
CMD, D inputs (referenced to CK) in eMMC mode						
t_{ISU}	Input setup time HS	fpp = 50 MHz	0	-	-	ns
t_{IH}	Input hold time HS	fpp = 50 MHz	6	-	-	
CMD, D outputs (referenced to CK) in eMMC mode						
t_{OV}	Output valid time HS	fpp = 50 MHz	-	3.5	5	ns
t_{OH}	Output hold time HS	fpp = 50 MHz	2	-	-	

1. Guaranteed by characterization results.
2. C_{load} = 20 pF

Table 78. RTC characteristics

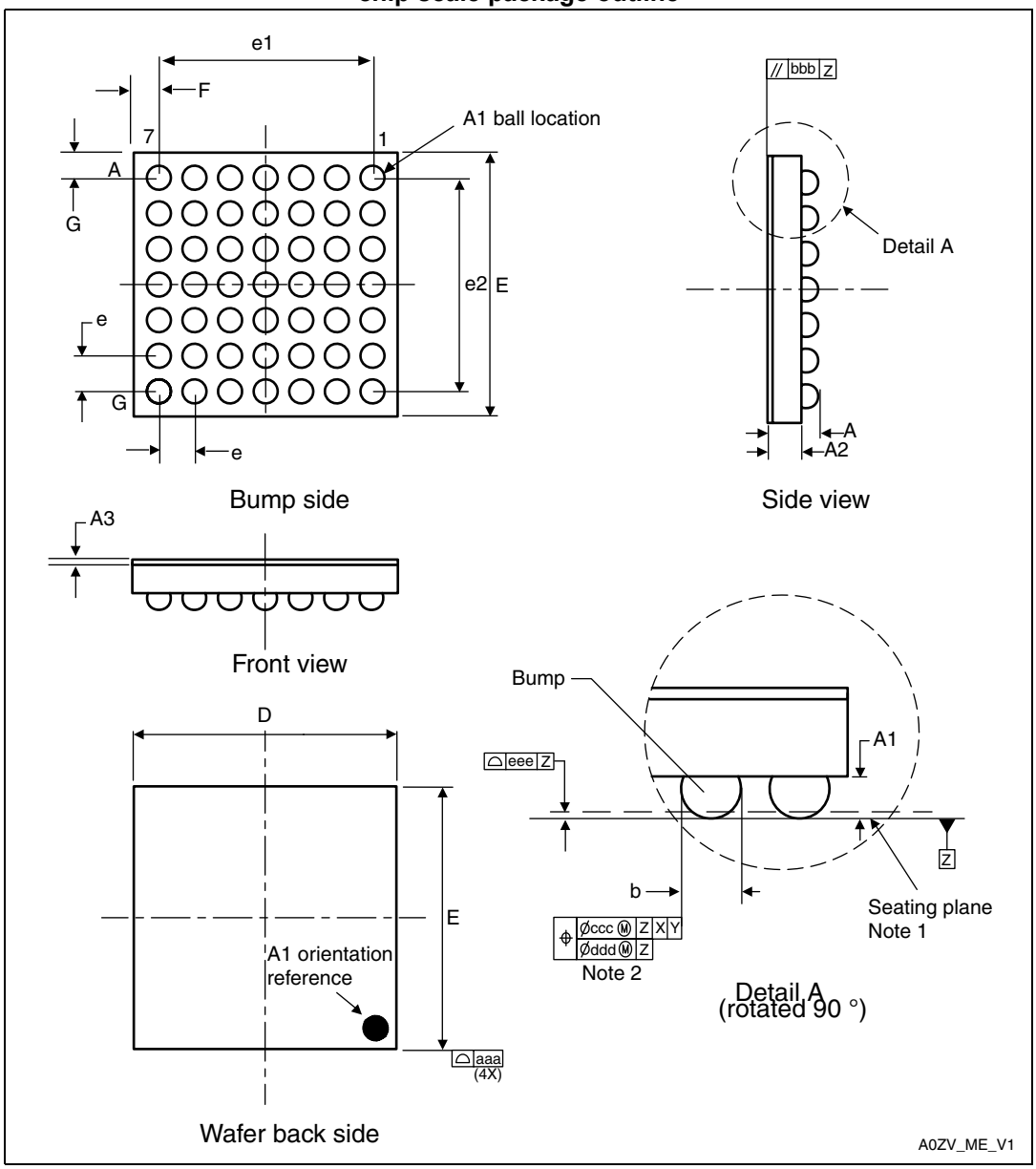
Symbol	Parameter	Conditions	Min	Max
-	f_{PCLK1}/RTCCLK frequency ratio	Any read/write operation from/to an RTC register	4	-

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

7.1 WLCSP49 package information

Figure 46. WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scale package outline



1. Drawing is not to scale.

Table 79. WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.964	2.999	3.034	0.1167	0.1181	0.1194
E	3.150	3.185	3.220	0.1240	0.1254	0.1268
e	-	0.400	-	-	0.0157	-
e1	-	2.400	-	-	0.0945	-
e2	-	2.400	-	-	0.0945	-
F	-	0.2995	-	-	0.0118	-
G	-	0.3925	-	-	0.0155	-
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ccc	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 47. WLCSP49 - 49-ball, 2.999 x 3.185 mm, 0.4 mm pitch wafer level chip scale recommended footprint

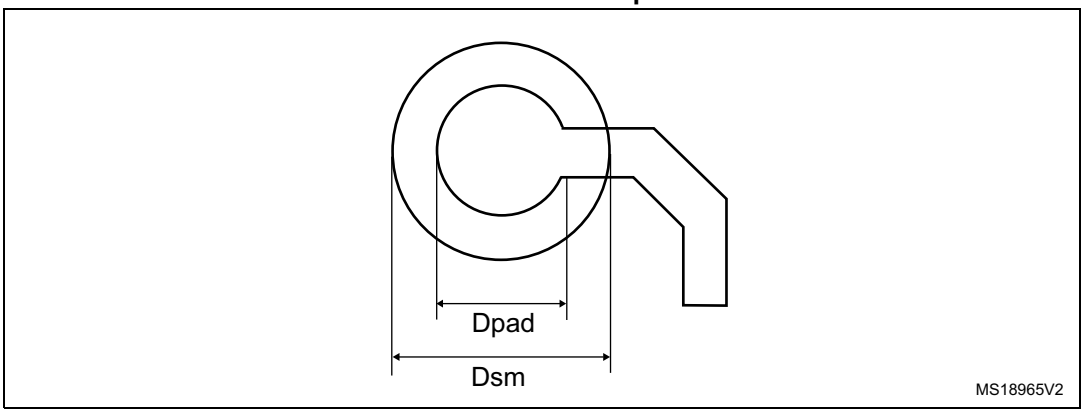
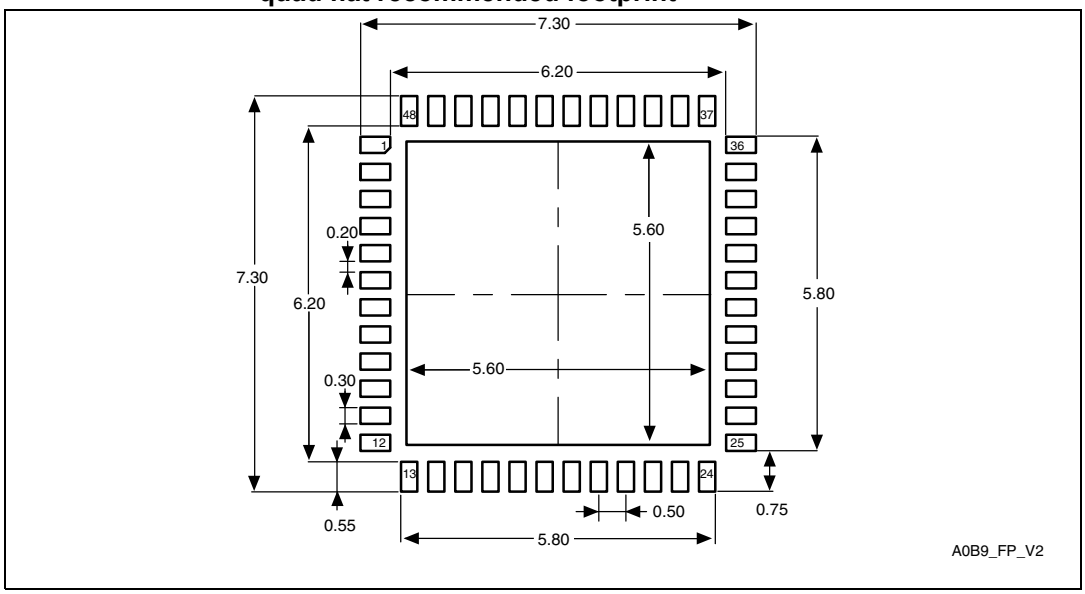


Table 81. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E2	5.500	5.600	5.700	0.2165	0.2205	0.2244
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-
ddd	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

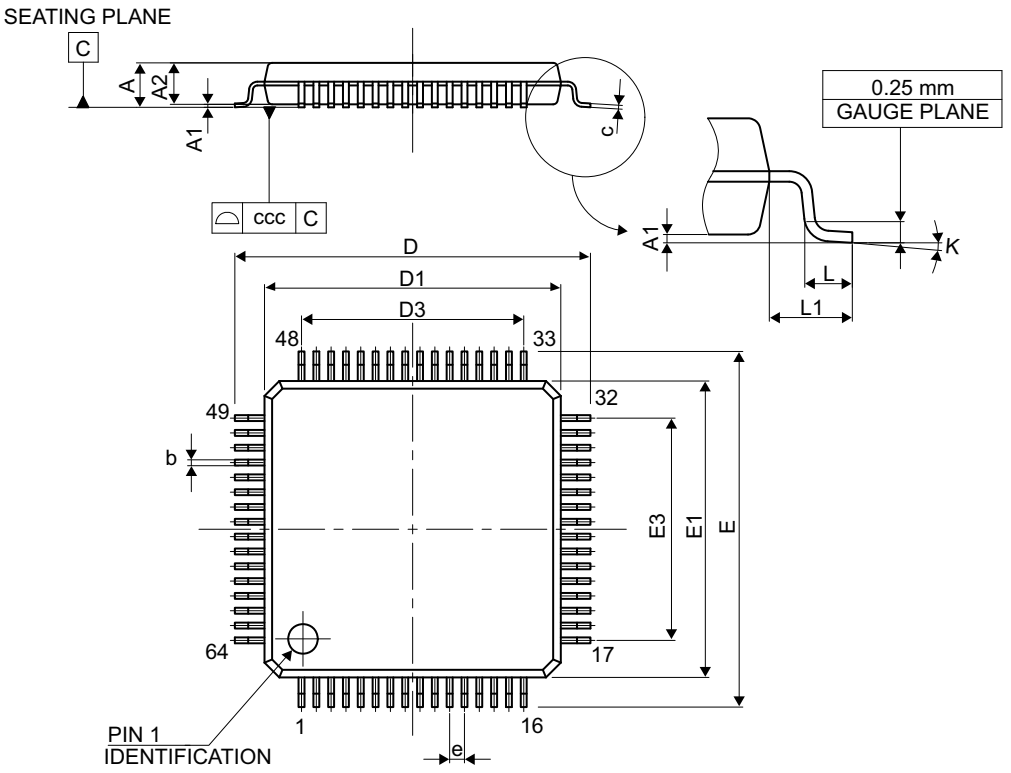
Figure 50. UFQFPN48 - 48-lead, 7 x 7 mm, 0.5 mm pitch, ultra thin fine pitch quad flat recommended footprint



1. Dimensions are in millimeters.

7.3 LQFP64 package information

Figure 52. LQFP64 - 64-pin, 10 x 10 mm, 64-pin low-profile quad flat package outline



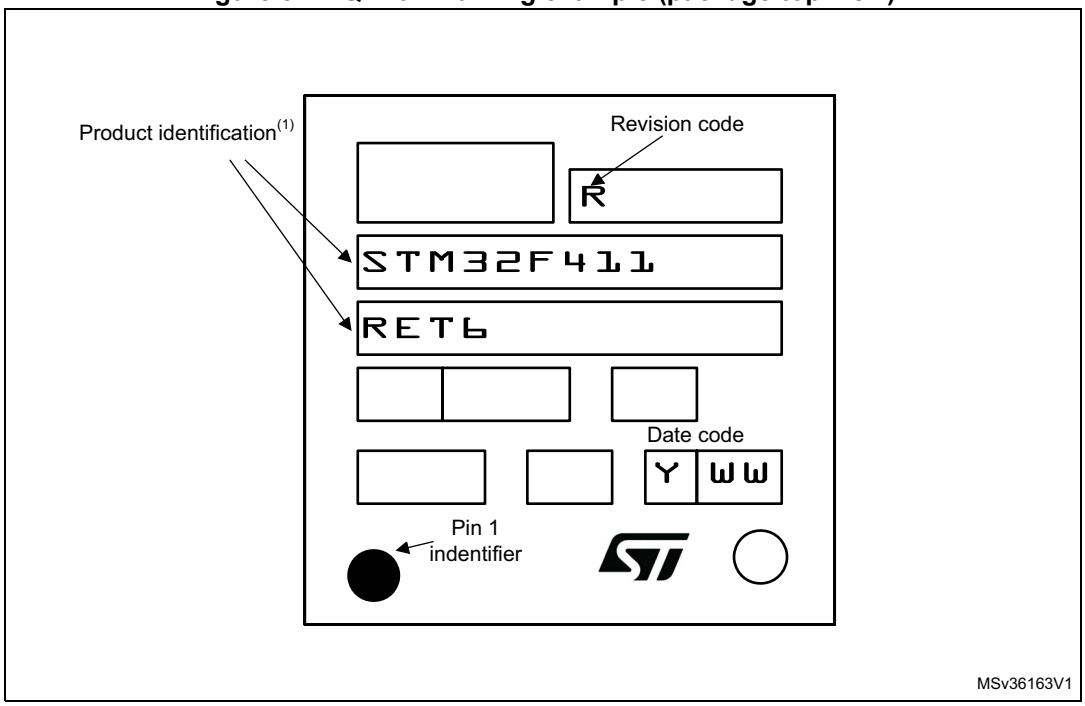
1. Drawing is not to scale.

Device marking for LQFP64

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

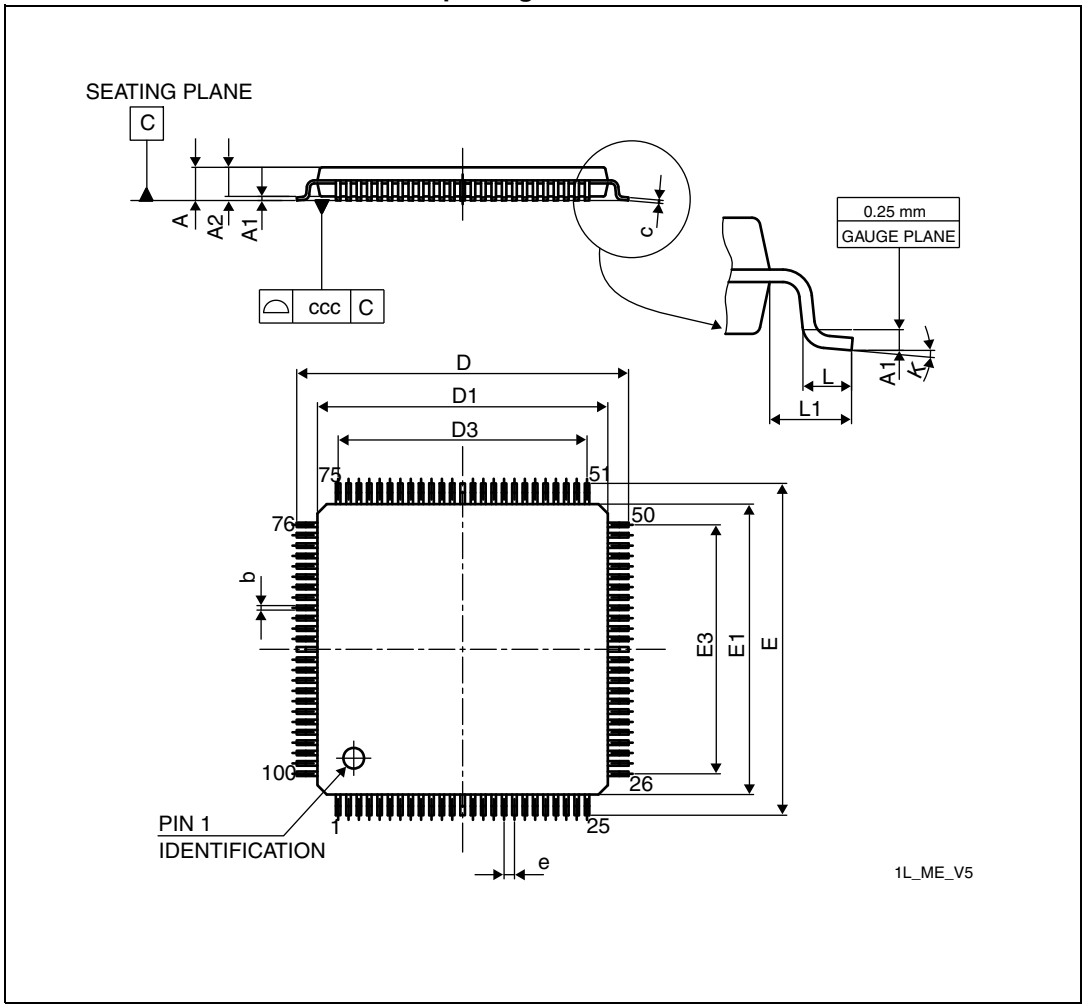
Figure 54. LQFP64 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

7.4 LQFP100 package information

Figure 55. LQFP100 - 100-pin, 14 x 14 mm, 100-pin low-profile quad flat package outline



1. Drawing is not to scale.